Martin Eickhoff

List of Publications by Year
in descending order

190 papers	7,449 citations	57758 44 h-index	64796 79 g-index
195 all docs	195 docs citations	195 times ranked	6782 citing authors

#	Article	IF	Citations
1	Detection of Hydrogen Dissolved in Liquid Media: A Review and Outlook. Physica Status Solidi (A) Applications and Materials Science, 2022, 219, .	1.8	0
2	Comparing Coâ€catalytic Effects of ZrO_x, SmO_x, and Pt on CO_x Methanation over Coâ€based Catalysts Prepared by Double Flame Spray Pyrolysis. ChemCatChem, 2021, 13, 2815-2831.	3.7	12
3	Behavior of the Îµ-Ga₂O₃:Sn Evaporation During Laser-Assisted Atom Probe Tomography. Microscopy and Microanalysis, 2021, 27, 687-695.	0.4	3
4	Time-resolved cathodoluminescence investigations of AlN:Ge/GaN nanowire structures. Nano Express, 2021, 2, 034001.	2.4	3
5	Surface Microscopy of Atomic and Molecular Hydrogen from Field-Evaporating Semiconductors. Journal of Physical Chemistry C, 2021, 125, 17078-17087.	3.1	4
6	4D-STEM at interfaces to GaN: Centre-of-mass approach & NBED-disc detection. Ultramicroscopy, 2021, 228, 113321.	1.9	9
7	Luminescence probing of surface adsorption processes using InGaN/GaN nanowire heterostructure arrays. , 2020, , 239-270.		4
8	Rare-Earth-Doped Y₄Al₂O₉ Nanoparticles for Stable Light-Converting Phosphors. ACS Applied Nano Materials, 2020, 3, 699-710.	5.0	21
9	Controlled Laser-Thinning of MoS₂ Nanolayers and Transformation to Amorphous MoO_x for 2D Monolayer Fabrication. ACS Applied Nano Materials, 2020, 3, 7490-7498.	5.0	14
10	Consistent description of mesoscopic transport: Case study of current-dependent magnetoconductance in single GaN:Ge nanowires. Physical Review B, 2019, 100, .	3.2	6
11	Chemically Sensitive Photoluminescence of InGaN/GaN Nanowire Heterostructure Arrays. Proceedings (mdpi), 2019, 14, 43.	0.2	0
12	The Role of Polarity in Nonplanar Semiconductor Nanostructures. Nano Letters, 2019, 19, 3396-3408.	9.1	31
13	Electrical Polarization in AlN/GaN Nanodisks Measured by Momentum-Resolved 4D Scanning Transmission Electron Microscopy. Physical Review Letters, 2019, 122, 106102.	7.8	31
14	Ion sensitive AlGaN/GaN field-effect transistors with monolithically integrated wheatstone bridge for temperature- and drift compensation in enzymatic biosensors. Sensors and Actuators B: Chemical, 2018, 263, 20-26.	7.8	12
15	Optical emission of GaN/AlN quantum-wires â€“ the role of charge transfer from a nanowire template. Nanoscale, 2018, 10, 5591-5598.	5.6	12
16	Photoelectrochemical response of GaN, InGaN, and GaNP nanowire ensembles. Journal of Applied Physics, 2018, 123, 175703.	2.5	4
17	Flexible Modulation of Electronic Band Structures of Wide Band Gap GaN Semiconductors Using Bioinspired, Nonbiological Helical Peptides. Advanced Functional Materials, 2018, 28, 1704034.	14.9	9
18	Synthesis of SnO₂ Nanowires Using SnI₂ as Precursor and Their Application as Highâ€Performance Selfâ€Powered Ultraviolet Photodetectors. Physica Status Solidi (B): Basic Research, 2018, 255, 1700426.	1.5	10

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19	Passivation layers for nanostructured photoanodes: ultra-thin oxides on InGaN nanowires. Journal of Materials Chemistry A, 2018, 6, 565-573.	10.3	26
20	Influence of the atom source operating parameters on the structural and optical properties of In xGa 1 â˜' xN nanowires grown by plasma-assisted molecular beam epitaxy. Journal of Applied Physics, 2018, 124, 165703.	2.5	3
21	Photoluminescence Detection of Surface Oxidation Processes on InGaN/GaN Nanowire Arrays. ACS Sensors, 2018, 3, 2254-2260.	7.8	13
22	Suppression of the quantum-confined Stark effect in polar nitride heterostructures. Communications Physics, 2018, 1, .	5.3	14
23	Optical Analysis of Oxygen Selfâ€Diffusion in Ultrathin CeO₂ Layers at Low Temperatures. Advanced Energy Materials, 2018, 8, 1802120.	19.5	4
24	Dynamic Extracellular Imaging of Biochemical Cell Activity Using InGaN/GaN Nanowire Arrays as Nanophotonic Probes. Advanced Functional Materials, 2018, 28, 1802503.	14.9	7
25	Effects of the Fermi level energy on the adsorption of O ₂ to monolayer MoS ₂. 2D Materials, 2018, 5, 045025.	4.4	8
26	Photoluminescence Probing of Complex H₂O Adsorption on InGaN/GaN Nanowires. Nano Letters, 2017, 17, 615-621.	9.1	19
27	InGaN/GaN nanowires as a new platform for photoelectrochemical sensors â€“ detection of NADH. Biosensors and Bioelectronics, 2017, 94, 298-304.	10.1	47
28	Competitive adsorption of air constituents as observed on InGaN/GaN nano-optical probes. Sensors and Actuators B: Chemical, 2017, 250, 91-99.	7.8	12
29	Influence of the cluster constituentsâ€™ reactivity on the desorption/ionization process induced by neutral SO2 clusters. Journal of Chemical Physics, 2017, 146, 134705.	3.0	13
30	Bias-Controlled Spectral Response in GaN/AlN Single-Nanowire Ultraviolet Photodetectors. Nano Letters, 2017, 17, 4231-4239.	9.1	45
31	Study of the carrier transfer across the GaNP nanowire electrolyte interface by electron paramagnetic spin trapping. Applied Physics Letters, 2017, 110, 222101.	3.3	2
32	Bias-Controlled Optical Transitions in GaN/AlN Nanowire Heterostructures. ACS Nano, 2017, 11, 8758-8767.	14.6	10
33	Transport mechanisms in SnO₂:N,H thin film grown by chemical vapor deposition. Physica Status Solidi (B): Basic Research, 2017, 254, 1700003.	1.5	3
34	Evidence for nitrogen-related deep acceptor states in SnO2 grown by chemical vapor deposition. Journal of Applied Physics, 2017, 122, 205702.	2.5	4
35	Three dimensional reconstruction of InGaN nanodisks in GaN nanowires: Improvement of the nanowire sample preparation to avoid missing wedge effects. Journal of Crystal Growth, 2017, 475, 202-207.	1.5	3
36	Nitrogen incorporation in SnO₂ thin films grown by chemical vapor deposition. Physica Status Solidi (B): Basic Research, 2016, 253, 1087-1092.	1.5	17

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37	Short-wavelength, mid- and far-infrared intersubband absorption in nonpolar GaN/Al(Ga)N heterostructures. Japanese Journal of Applied Physics, 2016, 55, 05FG05.	1.5	9
38	Hydrogen induced mobility enhancement in RF sputtered Cu2O thin films. Journal of Applied Physics, 2016, 120, 185705.	2.5	9
39	Shift of optical absorption edge in SnO2 films with high concentrations of nitrogen grown by chemical vapor deposition. Journal of Applied Physics, 2016, 119, .	2.5	13
40	Ge doping of GaN beyond the Mott transition. Journal Physics D: Applied Physics, 2016, 49, 445301.	2.8	36
41	Interfacial properties of self-assembled GaN nanowires on pre-processed Al2O3(0001) surfaces. Materials Science in Semiconductor Processing, 2016, 55, 46-50.	4.0	3
42	UV Photosensing Characteristics of Nanowire-Based GaN/AlN Superlattices. Nano Letters, 2016, 16, 3260-3267.	9.1	53
43	Optical manipulation of a multilevel nuclear spin in ZnO: Master equation and experiment. Physical Review B, 2016, 93, .	3.2	1
44	Plasma assisted molecular beam epitaxy of Cu2O on MgO(001): Influence of copper flux on epitaxial orientation. Journal of Crystal Growth, 2016, 436, 87-91.	1.5	11
45	Luminescent properties of ZnO and ZnMgO epitaxial layers under high hydrostatic pressure. Journal of Alloys and Compounds, 2016, 672, 125-130.	5.5	8
46	In situ monitoring of myenteric neuron activity using acetylcholinesterase-modified AlGaN/GaN solution-gate field-effect transistors. Biosensors and Bioelectronics, 2016, 77, 1048-1054.	10.1	5
47	Structural and electronic properties of GaN nanowires with embedded InxGa1â^'xN nanodisks. Journal of Applied Physics, 2015, 118, 034301.	2.5	11
48	Effect of Water Vapor and Surface Morphology on the Low Temperature Response of Metal Oxide Semiconductor Gas Sensors. Materials, 2015, 8, 6570-6588.	2.9	22
49	Electrical transport properties of Ge-doped GaN nanowires. Nanotechnology, 2015, 26, 135704.	2.6	19
50	Long-lived excitons in GaN/AlN nanowire heterostructures. Physical Review B, 2015, 91, .	3.2	17
51	Nonpolarm-plane GaN/AlGaN heterostructures with intersubband transitions in the 5â€“10 THz band. Nanotechnology, 2015, 26, 435201.	2.6	26
52	Integration of an opto-chemical detector based on group III-nitride nanowire heterostructures. Applied Optics, 2015, 54, 839.	1.8	5
53	Self-assembly of ordered wurtzite/rock salt heterostructuresâ€”A new view on phase separation in MgxZn1â^'xO. Journal of Applied Physics, 2015, 118, .	2.5	4
54	Doping-Induced Universal Conductance Fluctuations in GaN Nanowires. Nano Letters, 2015, 15, 7822-7828.	9.1	18

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55	Quantitative analysis of immobilized penicillinase using enzyme-modified AlGaN/GaN field-effect transistors. Biosensors and Bioelectronics, 2015, 64, 605-610.	10.1	15
56	Group III-Nitride Chemical Nanosensors with Optical Readout. Springer Series on Chemical Sensors and Biosensors, 2014, , 311-338.	0.5	3
57	Screening of the quantum-confined Stark effect in AlN/GaN nanowire superlattices by germanium doping. Applied Physics Letters, 2014, 104, .	3.3	23
58	High Precision, Electrochemical Detection of Reversible Binding of Recombinant Proteins on Wide Bandgap GaN Electrodes Functionalized with Biomembrane Models. Advanced Functional Materials, 2014, 24, 4927-4934.	14.9	4
59	Detection of oxidising gases using an optochemical sensor system based on GaN/InGaN nanowires. Sensors and Actuators B: Chemical, 2014, 197, 87-94.	7.8	52
60	Intraband Absorption in Self-Assembled Ge-Doped GaN/AlN Nanowire Heterostructures. Nano Letters, 2014, 14, 1665-1673.	9.1	33
61	Probing the Internal Electric Field in GaN/AlGaN Nanowire Heterostructures. Nano Letters, 2014, 14, 5118-5122.	9.1	23
62	Bandgap engineering in a nanowire: self-assembled 0, 1 and 2D quantum structures. Materials Today, 2013, 16, 213-219.	14.2	30
63	Nanostructure and strain in InGaN/GaN superlattices grown in GaN nanowires. Nanotechnology, 2013, 24, 435702.	2.6	58
64	A review of MBE grown 0D, 1D and 2D quantum structures in a nanowire. Journal of Materials Chemistry C, 2013, 1, 4300.	5.5	66
65	Effects of interface geometry on the thermoelectric properties of laterally microstructured ZnOâ€based thin films. Physica Status Solidi (A) Applications and Materials Science, 2013, 210, 119-124.	1.8	6
66	Optical properties of GaN-based nanowires containing a single Al_{0.14}Ga_{0.86}N/GaN quantum disc. Nanotechnology, 2013, 24, 125201.	2.6	10
67	Probing carrier populations in ZnO quantum wells by screening of the internal electric fields. Physical Review B, 2013, 87, .	3.2	5
68	Micro-optical system as integration platform for III-N nanowire based opto-chemical detectors. Proceedings of SPIE, 2013, , .	0.8	3
69	III-nitride nanostructures for optical gas detection and pH sensing. Proceedings of SPIE, 2013, , .	0.8	4
70	Radical formation at the gallium nitride nanowireâ€“electrolyte interface by photoactivated charge transfer. Nanotechnology, 2013, 24, 325701.	2.6	6
71	Contactless electroreflectance studies of free exciton binding energy in Zn1-xMgxO epilayers. Applied Physics Letters, 2013, 103, 251908.	3.3	13
72	Germanium doping of self-assembled GaN nanowires grown by plasma-assisted molecular beam epitaxy. Journal of Applied Physics, 2013, 114, .	2.5	41

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73	Accurate determination of optical bandgap and lattice parameters of Zn1â€“xMgxO epitaxial films (0â‰¤xâ‰¤0.3) grown by plasma-assisted molecular beam epitaxy on a-plane sapphire. Journal of Applied Physics, 2013, 113, 233512.	2.5	25
74	InGaN/GaN quantum dots as optical probes for the electric field at the GaN/electrolyte interface. Journal of Applied Physics, 2013, 114, 074313.	2.5	4
75	Growth study of nonpolar Zn_{1â^’x}Mg_xO epitaxial films on a-plane bulk ZnO by plasma-assisted molecular beam epitaxy. Applied Physics Letters, 2012, 101, 122106.	3.3	4
76	ZnO/(ZnMg)O single quantum wells with high Mg content graded barriers. Journal of Applied Physics, 2012, 111, 113504.	2.5	12
77	Electrochemical properties of GaN nanowire electrodesâ€”influence of doping and control by external bias. Nanotechnology, 2012, 23, 165701.	2.6	22
78	Polarity Assignment in ZnTe, GaAs, ZnO, and GaN-AlN Nanowires from Direct Dumbbell Analysis. Nano Letters, 2012, 12, 2579-2586.	9.1	161
79	Bias-Enhanced Optical pH Response of Group IIIâ€“Nitride Nanowires. Nano Letters, 2012, 12, 6180-6186.	9.1	60
80	Phonon-assisted luminescence of polar semiconductors: FrÃ¶hlich coupling versus deformation-potential scattering. Physical Review B, 2012, 85, .	3.2	27
81	Opto-chemical sensor system for the detection of H2 and hydrocarbons based on InGaN/GaN nanowires. Sensors and Actuators B: Chemical, 2012, 173, 120-126.	7.8	49
82	Self-assembled GaN quantum wires on GaN/AlN nanowire templates. Nanoscale, 2012, 4, 7517.	5.6	49
83	Binary copper oxide semiconductors: From materials towards devices. Physica Status Solidi (B): Basic Research, 2012, 249, 1487-1509.	1.5	547
84	Intra-excitonic relaxation dynamics in ZnO. Applied Physics Letters, 2011, 99, 231910.	3.3	9
85	Optical properties of wurtzite/zinc-blende heterostructures in GaN nanowires. Journal of Applied Physics, 2011, 110, .	2.5	62
86	Carrier dynamics in (ZnMg)O alloy materials. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 1149-1152.	0.8	1
87	GaN nanodiscs embedded in nanowires as optochemical transducers. Nanotechnology, 2011, 22, 275505.	2.6	59
88	Optical properties of MgZnO alloys: Excitons and exciton-phonon complexes. Journal of Applied Physics, 2011, 110, .	2.5	50
89	Carrier confinement in GaN/Al<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mi>x</mml:mi></mml:msub></mml:math>Ga<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mrow><mml:mn>1</mml:mn><mml:mo>â^’</mml:mo><mml:mi>x</mml:mi></mml:mrow></mml:msub></mml:math>N		

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91	Photocatalytic Cleavage of Selfâ€Assembled Organic Monolayers by UVâ€Induced Charge Transfer from GaN Substrates. Advanced Materials, 2010, 22, 2632-2636.	21.0	28
92	Investigation of carrier dynamics in Zn1â^'xMgxO by time-resolved photoluminescence. Journal of Luminescence, 2010, 130, 2256-2259.	3.1	15
93	Optical characterization of AlGaN/GaN quantum disc structures in single nanowires. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 2243-2245.	0.8	0
94	Pâ€type doping of semipolar GaN(11$ ar 2 $2) by plasmaâ€assisted molecularâ€beam epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 1913-1915.	0.8	6
95	Electron spin resonance of Zn1â^'xMgxO thin films grown by plasma-assisted molecular beam epitaxy. Applied Physics Letters, 2010, 97, 092102.	3.3	5
96	Origin of energy dispersion in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mtext>Al</mml:mtext></mml:mrow><mml:mi>x</mml:mi></mml:msub> quantum discs with low Al content. Physical Review B, 2010, 82, .	3.2	29
97	Photoluminescence polarization properties of single GaN nanowires containing<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mtext>Al</mml:mtext></mml:mrow><mml:mi>x</mml:mi></mml:msub> discs. Physical Review B, 2010, 81, .	3.2	28
98	On the Low-Temperature Response of Semiconductor Gas Sensors. Journal of Sensors, 2009, 2009, 1-17.	1.1	66
99	GaN quantum dots as optical transducers for chemical sensors. Applied Physics Letters, 2009, 94, 113108.	3.3	17
100	Optical properties and structural characteristics of ZnMgO grown by plasma assisted molecular beam epitaxy. Journal of Applied Physics, 2009, 105, .	2.5	93
101	Mg doping and its effect on the semipolar GaN(112Â¯2) growth kinetics. Applied Physics Letters, 2009, 95, 171908.	3.3	20
102	Strain effects and phononâ€“plasmon coupled modes in Siâ€doped AlN. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 1183-1186.	1.8	6
103	Analysis of polarizationâ€dependent photoreflectance studies for c â€plane GaN films grown on a â€plane sapphire. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 773-779.	1.8	4
104	Ultrathin GaN/AlN/GaN solution-gate field effect transistor with enhanced resolution at low source-gate voltage. Sensors and Actuators B: Chemical, 2009, 142, 304-307.	7.8	25
105	Gallium nitride electrodes for membrane-based electrochemical biosensors. European Physical Journal E, 2009, 30, 233-8.	1.6	14
106	Triple-twin domains in Mg doped GaN wurtzite nanowires: structural and electronic properties of this zinc-blende-like stacking. Nanotechnology, 2009, 20, 145704.	2.6	84
107	GaN/AlN Axial Multi Quantum Well Nanowires for Optoelectronic Devices. , 2009, , .		0
108	A novel GaNâ€based multiparameter sensor system for biochemical analysis. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 2361-2363.	0.8	12

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109	Gas sensing properties of hydrogen-terminated diamond. Sensors and Actuators B: Chemical, 2008, 133, 156-165.	7.8	48
110	Optical properties of Si- and Mg-doped gallium nitride nanowires grown by plasma-assisted molecular beam epitaxy. Journal of Applied Physics, 2008, 104, .	2.5	93
111	Nucleation and growth of GaN nanorods on Si (111) surfaces by plasma-assisted molecular beam epitaxy - The influence of Si- and Mg-doping. Journal of Applied Physics, 2008, 104, .	2.5	136
112	The Surface Conductivity at the Diamond/Aqueous Electrolyte Interface. Journal of the American Chemical Society, 2008, 130, 4177-4181.	13.7	38
113	Functionalization of 6H-SiC surfaces with organosilanes. Applied Physics Letters, 2008, 92, 153301.	3.3	47
114	Stark shift of interband transitions in AlNâˆ•GaN superlattices. Applied Physics Letters, 2007, 90, 241906.	3.3	8
115	Dissociative Gas Sensing at Metal Oxide Surfaces. IEEE Sensors Journal, 2007, 7, 1675-1679.	4.7	20
116	GaN Quantum Dots as Optical Transducers in Field Effect Chemical Sensors. , 2007, , .		0
117	Gas Sensing Interactions at Hydrogenated Diamond Surfaces. IEEE Sensors Journal, 2007, 7, 1349-1353.	4.7	15
118	Selective etching of AlInN/GaN heterostructures for MEMS technology. Microelectronic Engineering, 2007, 84, 1152-1156.	2.4	14
119	Fully unstrained GaN on sacrificial AlN layers by nano-heteroepitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 2248-2251.	0.8	4
120	Modulation spectroscopy of AlGaN/GaN heterostructures: The influence of electron-hole interaction. Physica Status Solidi (A) Applications and Materials Science, 2007, 204, 447-458.	1.8	23
121	Fabrication of freestanding GaN microstructures using AlN sacrificial layers. Physica Status Solidi - Rapid Research Letters, 2007, 1, R10-R12.	2.4	6
122	SnO2:Sb â€“ A new material for high-temperature MEMS heater applications: Performance and limitations. Sensors and Actuators B: Chemical, 2007, 124, 421-428.	7.8	38
123	Luminescence properties of highly Si-doped AlN. Applied Physics Letters, 2006, 88, 071906.	3.3	36
124	New Materials for Chemical and Biosensors. Materials and Manufacturing Processes, 2006, 21, 253-256.	4.7	30
125	Direct biofunctionalization of semiconductors: A survey. Physica Status Solidi (A) Applications and Materials Science, 2006, 203, 3424-3437.	1.8	150
126	Nearly stress-free substrates for GaN homoepitaxy. Journal of Crystal Growth, 2006, 293, 462-468.	1.5	43

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127	Electroreflectance spectroscopy of Ptâ^•AlGaNâ^•GaN heterostructures exposed to gaseous hydrogen. Applied Physics Letters, 2006, 88, 024101.	3.3	16
128	Catalytic activity of enzymes immobilized on AlGaNâ^•GaN solution gate field-effect transistors. Applied Physics Letters, 2006, 89, 183901.	3.3	64
129	Impact of silicon incorporation on the formation of structural defects in AlN. Journal of Applied Physics, 2006, 100, 113531.	2.5	19
130	Phase transition by Mg doping of N-face polarity GaN. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 2216-2219.	0.8	2
131	Electrochemical stabilization of crystalline silicon with aromatic self-assembled monolayers in aqueous electrolytes. Physica Status Solidi (B): Basic Research, 2005, 242, 2838-2845.	1.5	5
132	Mn-rich clusters in GaN: Hexagonal or cubic symmetry?. Applied Physics Letters, 2005, 86, 131927.	3.3	58
133	Highly Si-doped AlN grown by plasma-assisted molecular-beam epitaxy. Applied Physics Letters, 2005, 86, 192108.	3.3	43
134	Chemical functionalization of GaN and AlN surfaces. Applied Physics Letters, 2005, 87, 263901.	3.3	128
135	Influence of thermal oxidation on the electronic properties of Pt Schottky contacts on GaN grown by molecular-beam epitaxy. Applied Physics Letters, 2005, 86, 083507.	3.3	13
136	Determination of the polarization discontinuity at the AlGaNâ^•GaN interface by electroreflectance spectroscopy. Applied Physics Letters, 2005, 86, 181912.	3.3	26
137	Recording of cell action potentials with AlGaNâ^•GaN field-effect transistors. Applied Physics Letters, 2005, 86, 033901.	3.3	112
138	Electron injection-induced effects in Mn-doped GaN. Journal of Applied Physics, 2004, 96, 3556-3558.	2.5	14
139	Structural and interface properties of an AlN diamond ultraviolet light emitting diode. Applied Physics Letters, 2004, 85, 3699-3701.	3.3	13
140	Piezoresistive properties of single crystalline, polycrystalline, and nanocrystalline n-type 3C-SiC. Journal of Applied Physics, 2004, 96, 2872-2877.	2.5	40
141	Polytype transition of N-face GaN:Mg from wurtzite to zinc-blende. Journal of Applied Physics, 2004, 96, 3709-3715.	2.5	18
142	Influence of crystal defects on the piezoresistive properties of 3Câ€“SiC. Journal of Applied Physics, 2004, 96, 2878-2888.	2.5	23
143	Direct Observation of Mn Clusters in GaN by X-ray Scanning Microscopy. Japanese Journal of Applied Physics, 2004, 43, L695-L697.	1.5	11
144	Improved 3C-SiC Films Epitaxially Grown on Si by Flash Lamp Processing. Journal of the Electrochemical Society, 2004, 151, G136.	2.9	16

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145	Vertical transport in group III-nitride heterostructures and application in AlN/GaN resonant tunneling diodes. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 2210-2227.	0.8	49
146	Photoreflectance studies of (Al)Ga- and N-face AlGaN/GaN heterostructures. Thin Solid Films, 2004, 450, 155-158.	1.8	19
147	Temperature-dependent electric fields in GaN Schottky diodes studied by electroreflectance. Thin Solid Films, 2004, 450, 163-166.	1.8	1
148	Anisotropic propagation of surface acoustic waves on nitride layers. Superlattices and Microstructures, 2004, 36, 815-823.	3.1	10
149	Influence of crystal quality on the electronic properties of n-type 3C-SiC grown by low temperature low pressure chemical vapor deposition. Journal of Applied Physics, 2004, 95, 7908-7917.	2.5	24
150	High quality heteroepitaxial AlN films on diamond. Journal of Applied Physics, 2004, 96, 895-902.	2.5	38
151	AlxGa1â€“xNâ€”A New Material System for Biosensors. Advanced Functional Materials, 2003, 13, 841-846.	14.9	146
152	Electronics and sensors based on pyroelectric AlGaN/GaN heterostructures. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 1878-1907.	0.8	65
153	Electronics and sensors based on pyroelectric AlGaN/GaN heterostructures - Part B: Sensor applications. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 1908-1918.	0.8	124
154	Influence of surface oxides on hydrogen-sensitive Pd:GaN Schottky diodes. Applied Physics Letters, 2003, 83, 773-775.	3.3	96
155	pH response of GaN surfaces and its application for pH-sensitive field-effect transistors. Applied Physics Letters, 2003, 83, 177-179.	3.3	264
156	AlN/Diamond np-junctions. Diamond and Related Materials, 2003, 12, 1873-1876.	3.9	25
157	AlN/diamond heterojunction diodes. Applied Physics Letters, 2003, 82, 290-292.	3.3	92
158	Hydrosilylation of crystalline silicon (111) and hydrogenated amorphous silicon surfaces: A comparative x-ray photoelectron spectroscopy study. Journal of Applied Physics, 2003, 94, 2289-2294.	2.5	49
159	Exciton quenching in Pt/GaN Schottky diodes with Ga- and N-face polarity. Applied Physics Letters, 2003, 82, 1712-1714.	3.3	16
160	Thermal stability of Pt- and Ni-based Schottky contacts on GaN and Al0.31Ga0.69N. Semiconductor Science and Technology, 2002, 17, L47-L54.	2.0	40
161	Pyroelectric properties of Al(In)GaN/GaN hetero- and quantum well structures. Journal of Physics Condensed Matter, 2002, 14, 3399-3434.	1.8	864
162	Hydrogen response mechanism of Ptâ€“GaN Schottky diodes. Applied Physics Letters, 2002, 80, 1222-1224.	3.3	197

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163	GaN-based heterostructures for sensor applications. Diamond and Related Materials, 2002, 11, 886-891.	3.9	150
164	Nanotechnology for SAW devices on AlN epilayers. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 93, 154-158.	3.5	34
165	Group III-nitride-based gas sensors for combustion monitoring. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 93, 207-214.	3.5	79
166	Observation of ion-induced changes in the channel current of high electron mobility AlGaN/GaN transistors (HEMT). Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 93, 143-146.	3.5	17
167	Gas sensitive GaN/AlGaN-heterostructures. Sensors and Actuators B: Chemical, 2002, 87, 425-430.	7.8	179
168	Novel Sensor Applications of group-III nitrides. Materials Research Society Symposia Proceedings, 2001, 693, 253.	0.1	2
169	Etching characteristics and mechanical properties of a-SiC:H thin films. Sensors and Actuators A: Physical, 2001, 94, 87-94.	4.1	35
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